

TrenchDMOS[™]

General Description

The AAT8107 low threshold 20V, P-channel MOS-FET is a member of AnalogicTech's TrenchDMOS product family. Using an ultra-high density proprietary TrenchDMOS technology, the AAT8107 is designed for use as a load switch in battery-powered applications and protection in battery packs.

Features

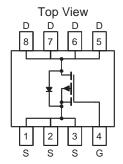
- $V_{DS(MAX)} = -20V$ $I_{D(MAX)}^{1} = -6.5A @ 25^{\circ}C$
- Low $R_{DS(ON)}$:

 35m Ω @ $V_{GS} = -4.5V$
 - $60m\Omega @ V_{GS} = -2.5V$

Applications

- **Battery Packs**
- Battery-Powered Portable Equipment

SOP-8L Package



Absolute Maximum Ratings

 $T_A = 25$ °C, unless otherwise noted.

| Symbol | Description | Value | Units | | |
|-------------------|-------------------------------------------------------------|---------------------|-------|---|--|
| V_{DS} | Drain-Source Voltage | -20 | V | | |
| V_{GS} | Gate-Source Voltage | ±12 | | | |
| I _D | Continuous Drain Current @ T _J =150°C¹ | $T_A = 25^{\circ}C$ | ±6.5 | | |
| | | $T_A = 70$ °C | ±5.2 | Α | |
| I_{DM} | Pulsed Drain Current ² | ±32 | ^ | | |
| I _S | Continuous Source Current (Source-Drain Diode) ¹ | -1.7 | | | |
| P _D | Maximum Power Dissipation ¹ | $T_A = 25^{\circ}C$ | 2.5 | W | |
| | | $T_A = 70$ °C | 1.6 | | |
| T_J , T_{STG} | Operating Junction and Storage Temperature Range | -55 to 150 | °C | | |

Thermal Characteristics

| Symbol | Description | Value | Units |
|-------------------|---------------------------------------------------------------|-------|-------|
| $R_{	heta JA}$ | Typical Junction-to-Ambient Steady State ¹ 80 | | |
| R _{0JA2} | Maximum Junction-to-Ambient t<10 Seconds ¹ 50 °C/W | | °C/W |
| $R_{\theta JF}$ | Typical Junction-to-Foot1 | 27 | |

^{1.} Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 10-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. R_{θJF} is guaranteed by design; however, R_{eCA} is determined by the PCB design. Actual maximum continuous current is limited by the application's design.

^{2.} Pulse test: Pulse Width = 300µs.



Electrical Characteristics

 $T_J = 25$ °C, unless otherwise noted.

| Symbol | Description | Conditions | Min | Тур | Max | Units |
|---------------------|----------------------------------------------|-----------------------------------------------------------------------------------|------|----------|----------|-------|
| DC Chara | acteristics | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | | | V |
| R _{DS(ON)} | Drain-Source On-Resistance ¹ | $V_{GS} = -4.5V$, $I_{D} = -6.5A$ $V_{GS} = -2.5V$, $I_{D} = -5.0A$ | | 27 46 | 35 60 | mΩ |
| I _{D(ON)} | On-State Drain Current ¹ | $V_{GS} = -4.5V$, $V_{DS} = 5V$ (Pulsed) | -32 | 10 | - 00 | Α |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_{D} = -250 \mu A$ | -0.6 | | | V |
| I _{GSS} | Gate-Body Leakage Current | $V_{GS} = \pm 12V, V_{DS} = 0V$ | | | ±100 | nA |
| I _{DSS} | Drain Source Leakage Current | $V_{GS} = 0V, V_{DS} = -20V$ $V_{GS} = 0V, V_{DS} = -16V, T_{J} = 70^{\circ}C$ | | | -1 -5 | μΑ |
| 9 _{fs} | Forward Transconductance ¹ | $V_{DS} = -5V, I_{D} = -6.5A$ | | 12 | | S |
| Dynamic | Characteristics ² | | | | | |
| Q_{G} | Total Gate Charge | $V_{DS} = -15V, R_D = 2.3\Omega, V_{GS} = -4.5V$ | | 13.6 | | |
| Q_{GS} | Gate-Source Charge | $V_{DS} = -15V$, $R_{D} = 2.3\Omega$, $V_{GS} = -4.5V$ | | 2.3 | | nC |
| Q_{GD} | Gate-Drain Charge | $V_{DS} = -15V, R_D = 2.3\Omega, V_{GS} = -4.5V$ | | 5.5 | | |
| $t_{D(ON)}$ | Turn-On Delay | $V_{DS} = -15V$, $R_{D} = 2.3\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$ | | 10 | | |
| t _R | Turn-On Rise Time | $V_{DS} = -15V$, $R_{D} = 2.3\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$ | | 35 | | no |
| t _{D(OFF)} | Turn-Off Delay | $V_{DS} = -15V$, $R_{D} = 2.3\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$ | | 38 | | ns |
| t _F | Turn-Off Fall Time | $V_{DS} = -15V$, $R_{D} = 2.3\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$ | | 50 | | |
| Source-D | rain Diode Characteristics | | | | | |
| V_{SD} | Source-Drain Forward Voltage ¹ | $V_{GS} = 0, I_{S} = -6.5A$ | | | -1.5 | V |
| I _S | Continuous Diode Current ³ | | | | -1.7 | Α |

^{1.} Pulse test: Pulse Width = 300µs.

^{2.} Guaranteed by design. Not subject to production testing.

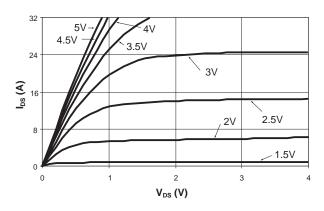
^{3.} Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 10-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. $R_{\theta JF}$ is guaranteed by design; however, $R_{\theta CA}$ is determined by the PCB design. Actual maximum continuous current is limited by the application's design.



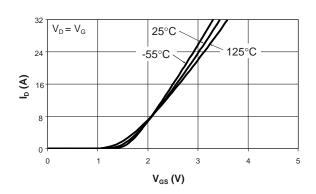
Typical Characteristics

 $T_{\rm J} = 25^{\circ}$ C, unless otherwise noted.

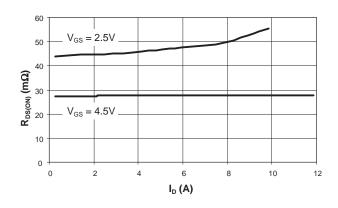
Output Characteristics



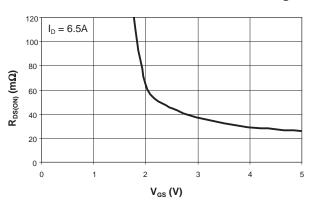
Transfer Characteristics



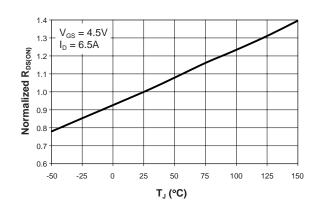
On-Resistance vs. Drain Current



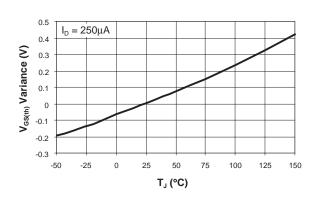
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Threshold Voltage

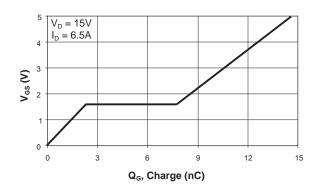




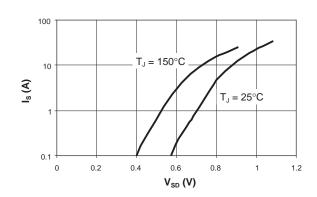
Typical Characteristics

 $T_{\perp} = 25^{\circ}$ C, unless otherwise noted.

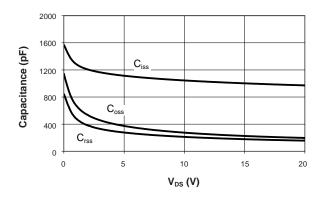
Gate Charge



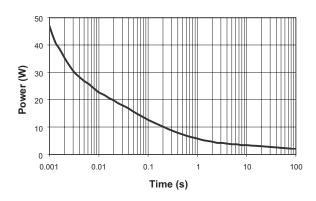
Source-Drain Diode Forward Voltage



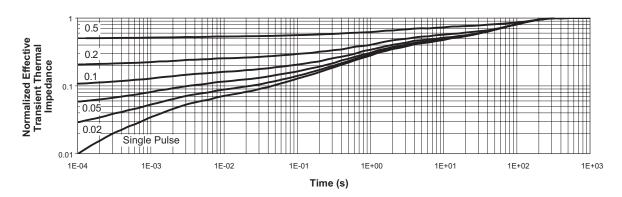
Capacitance



Single Pulse Power, Junction to Ambient



Transient Thermal Response, Junction to Ambient



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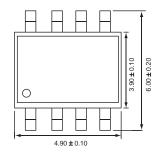


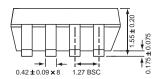
Ordering Information

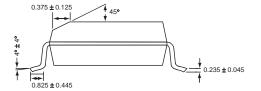
| Package | Marking | Part Number (Tape and Reel) ¹ |
|---------|---------|------------------------------------------|
| SOP-8 | 8107 | AAT8107IAS-T1 |

Package Information

SOP-8







All dimensions in millimeters.

^{1.} Sample stock is generally held on all part numbers listed in BOLD.



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